## **ABSTRACT**

A method for making a semiconductor device is described. That method comprises forming a first dielectric layer on a substrate, then forming a trench within the first dielectric layer. After forming a second dielectric layer on the substrate, a first metal layer is formed within the trench on a first part of the second dielectric layer. A second metal layer is then formed on the first metal layer and on a second part of the second dielectric layer.

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